

**AMENDMENTS TO THE SPECIFICATION**

**Please replace the first complete paragraph on page 7 with the following amended paragraph.**

Fourth, in case of forming an insulation film on the side surface of the porous insulation film, there was a problem that the sectional area reduces and as the result wiring resistance increases, because an insulation film is formed on the bottom of the wiring trench as well as the side surface when fully protecting the side surface of the porous insulation film (refer to Fig. 2E). Typical technical documents including such a problem are, for instance, Japanese patent No.

~~003323005332305~~ and Japanese laid open patent (unexamined) ~~2003-~~  
~~668850~~2003-68850. So, there has been desired a technology enabling to form the insulation film only on the side surface of the wiring trench or via hole with high control performance.